INTEGRATED CIRCUITS, SILICON MONOLITHIC,

BIPOLAR, DUAL J-K FLIP-FLOPS WITH CLEAR,

BASED ON TYPE 54LS107A

ESCC Detail Specification No. 9203/020

ISSUE 1

October 2002

Document Custodian: European Space Agency - see https://escies.org

LEGAL DISCLAIMER AND COPYRIGHT

european space agency
agence spatiale européenne

Pages 1 to 30

INTEGRATED CIRCUITS, SILICON MONOLITHIC, BIPOLAR, DUAL J-K FLIP-FLOPS WITH CLEAR, BASED ON TYPE 54LS107A

ESA/SCC Detail Specification No. 9203/020

space components
coordination group

Issue/Rev.	Date	Approved by	
		SCCG Chairman	ESA Director General or his Deputy
Issue 5	November 1991	-	-
Revision 'A'	July 1992		
Revision 'B'	January 1995		

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
		This issue supersedes Issue 4 and incorporates all modifications agreed on the basis of the following DCR's:		
		Cover page		None
		DCN		None
		Table 1(a)	: Table amended	22881
		Figures 2(a), (b), (c)	: Imperial dimensions deleted	22881
		Figure 2(d)	: New figure	22881
		Figures 2(a) to (d)	: - Title of the notes amended	22881
			- Note 1, last sentence added	22881
			- Note 8, 'or terminals' added	22881
			- Note 9, rewritten	22881
			- Notes 11 and 12, new notes	22881
		Figure 3(a)	: - Title added	22881
			- Figure for chip carrier package added	22881
			- Comparison table added	22881
			- Note 1 added	22881
			: - Pins 10 and 13, CLR becomes $\overline{CLR}$ (editorial error)	None
		Figure 3(c)	: Note, 'and in ohms' deleted	None
		Para. 4.2.2	: Text amended (PIND deleted)	21048
		Para. 4.2.4	: Deviation replaced by 'None'	22919
		Para. 4.2.5	: Deviation replaced by 'None'	22919
		Para. 4.3.2	: Para. rewritten	23460
		Para. 4.4.2	: Para. rewritten	22881
		Para. 4.5.2	: Para. rewritten	22881
		Table 2	: $I_{OS\ min}$ limit changed	22824
		Table 3	: - $I_{OS\ min}$ limit changed	22824
			- V_{IL} changed in items 34 to 37 and 38 to 41	22824
		Table 6	: 'ditto' changed into 'As per Table 2'	None
'A'	July '92	P1. Cover Page		None
		P2. DCN		None
		P3. Table of Contents	: Amended as relevant	None
		P8. Figure 2(b)	: Reference to Note 6 changed to Note 10	23519
		P9. Figure 2(c)	: Reference to Note 6 changed to Note 10	23519
			: Dimension 'L' minimum amended	None
		P17. Para. 4.5.3	: Wording amended	23519
		P17. Para. 4.6.3	: 'and functional test sequence' deleted	23519
		P17. Para. 4.7.1	: 'T_{amb} =' added	23519
		P17. Para. 4.7.2	: 'burn-in' changed to 'power burn-in'	23519
		P17. Para. 4.7.3	: 'burn-in' changed to 'power burn-in'	23519
		P28. Para. 4.8	: Title amended	23519
'B'	Jan. '95	P1. Cover Page		None
		P2. DCN		None
		P6. Table 1(b)	: Nos. 2 and 3, Notes reference changed to "1" and "2" respectively.	23573
			: No. 6, Entry amended to include DIL and FP	23573
			: Notes renumbered to "2", "3" and "1" respectively and resequenced	23573
			: Old Note 2, new Note 3 amended	23573
			: New Note 4 added	23573
		P7. Figure 2(a)	: Drawing and Table amended	221033
		P8. Figure 2(b)	: Drawing and Table amended	221033
		P16. Para. 4.3.2	: Maximum weights amended	221047

TABLE OF CONTENTS

Page

TABLES

FIGURES

APPENDICES (Applicable to specific Manufacturers only)

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon, monolithic, low power bipolar Schottky, Dual J-K Flip-Flop with clear, based on Type 54LS107A. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000 the requirements for which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

Not applicable.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 TRUTH TABLE

As per Figure 3(b).

1.8 CIRCUIT SCHEMATIC

As per Figure 3(c).

1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).

TABLE 1(a) - TYPE VARIANTS

Variant	Case	Figure	Lead Material and/or Finish
01	FLAT	2(a)	D7
02	FLAT	2(a)	G4
05	DIL	2(b)	D7
06	DIL	2(b)	G4
07	DIL	2(c)	D7
08	DIL	2(c)	D3 or D4
11	CCP	2(d)	7
12	CCP	2(d)	4

TABLE 1(b) - MAXIMUM RATINGS

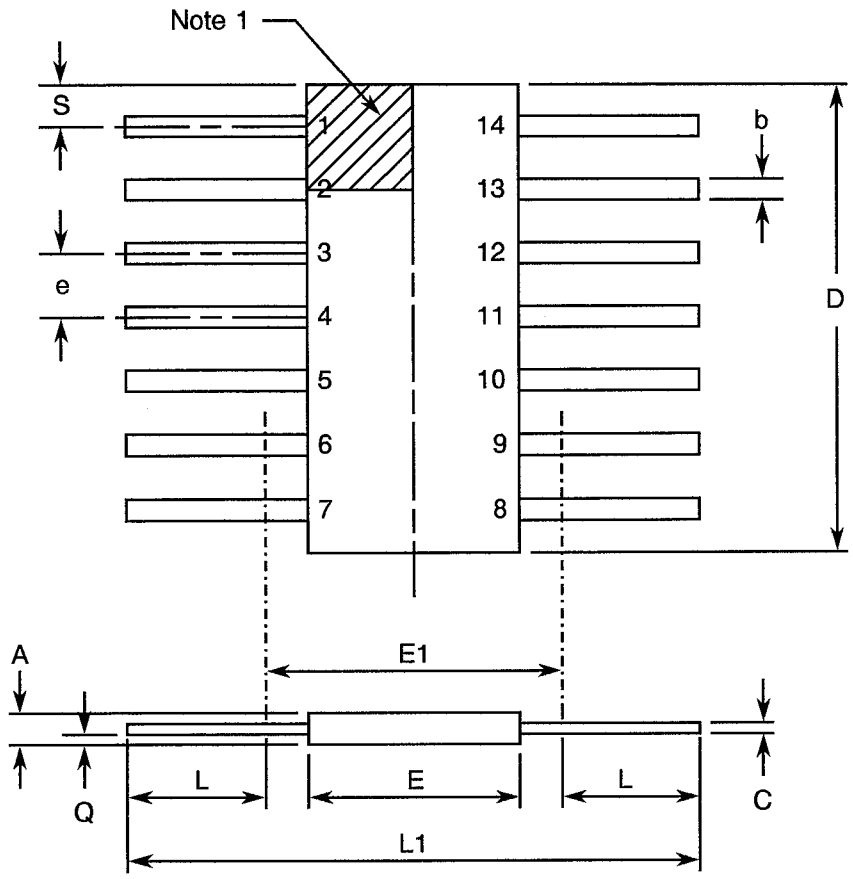
No.	Characteristics	Symbol	Maximum Ratings	Unit	Remarks
1	Supply Voltage	V_{CC}	-0.5 to 7.0	V	
2	Input Voltage	V_{IN}	-0.5 to 7.0	V	Note 1
3	Device Dissipation	P_D	33	mWdc	Note 2
4	Operating Temperature	T_{op}	-55 to +125	°C	
5	Storage Tempreature	T_{stg}	-65 to +150	°C	
6	Soldering Temperature For FP and DIL For CCP	T_{sol}	 +265 +245	°C	 Note 3 Note 4

NOTES

1. Input current limited to −18mA.
2. Must withstand added PD due to short circuit conditions (i.e. IOS) at one output for 5 seconds.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE

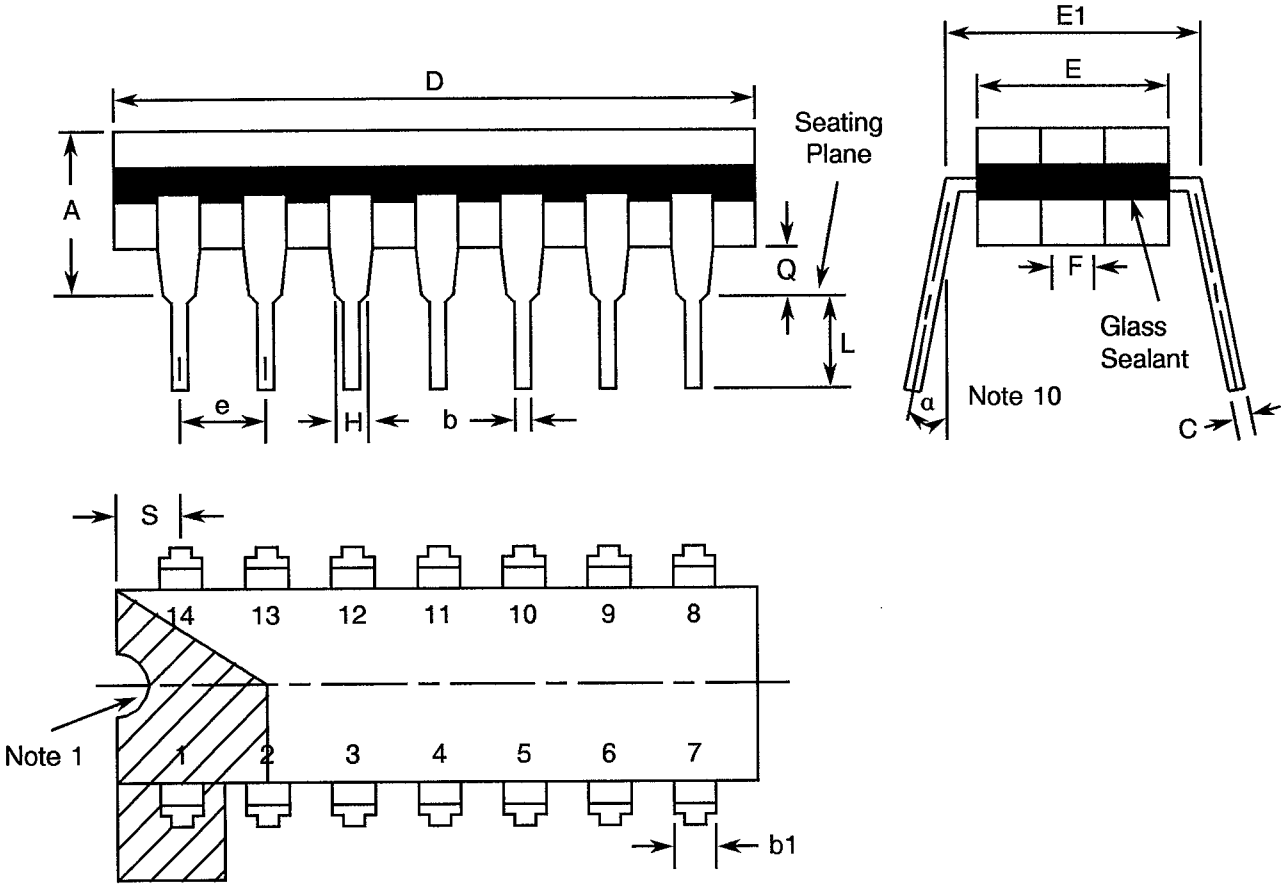


SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	1.27	2.03	
b	0.38	0.56	8
C	0.08	0.23	8
D	8.56	8.89	4
E	5.97	6.73	
E1	7.00 TYPICAL		4
e	1.27 TYPICAL		5, 9
L	6.86	8.00	8
L1	21.34	21.84	
Q	0.51	1.02	2
S	0.25	0.64	7

NOTES: See Page 11.

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - DUAL-IN-LINE PACKAGE

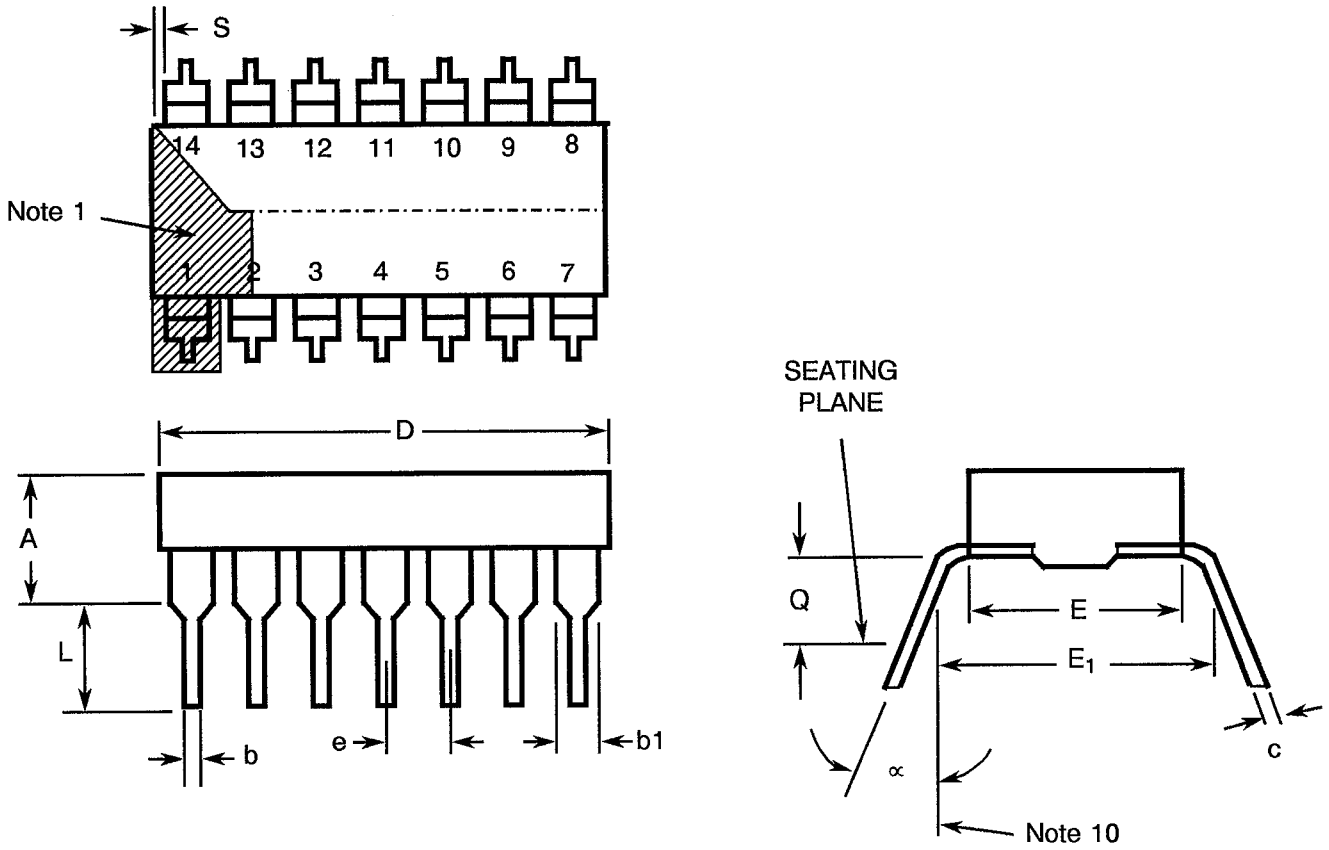


SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	-	5.08	
b	0.38	0.66	8
b1	-	1.78	8
C	0.20	0.44	8
D	19.18	19.94	4
E	6.22	7.62	4
E1	7.37	8.13	
e	2.54 TYPICAL		6, 9
F	1.27 TYPICAL		
H	0.76	-	8
L	3.30	5.08	8
Q	0.51	-	3
S	1.78	2.54	7
α	0°	15°	10

NOTES: See Page 11.

FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(c) - DUAL-IN-LINE PACKAGE

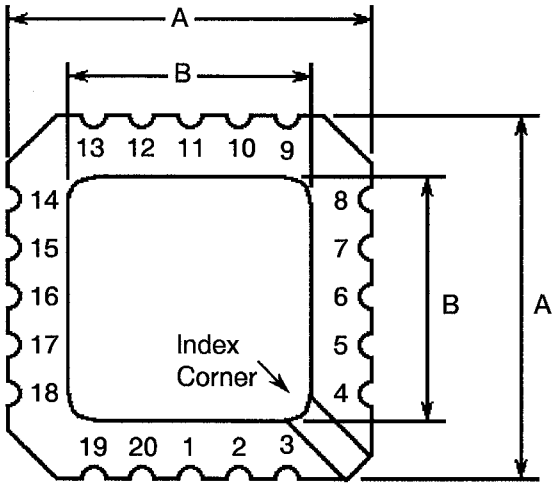


SYMBOL	MILLIMETRES		NOTES
	MIN.	MAX.	
A	-	5.08	
b	0.36	0.58	8
b_1	0.76	1.78	8
c	0.20	0.38	8
D	16.26	19.96	
E	5.59	7.87	
E_1	7.37	8.13	4
e	2.54 Typical		6, 9
L	3.18	5.08	
Q	0.38	2.03	3
S	0.25	1.35	7
∝	0°	15°	10

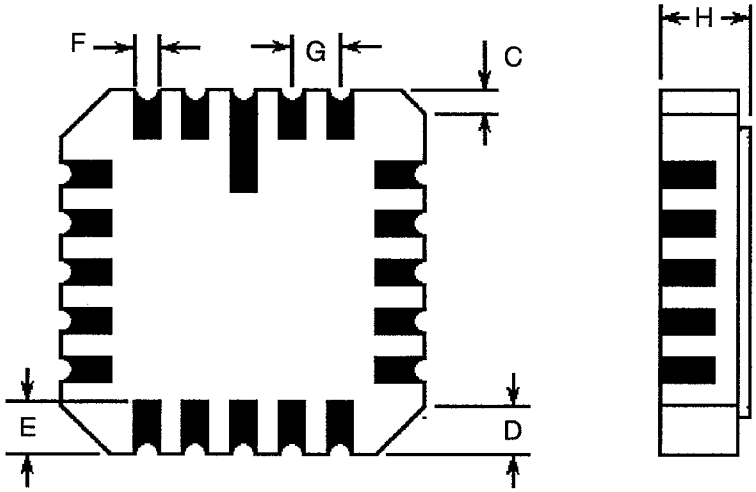
NOTES: See Page 11.

FIGURE 2 - PHYSICAL DIMENSIONS (Continued)

FIGURE 2(d) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)



20 Terminal



Symbol	Millimetres		Notes
	Min.	Max.	
A	8.687	9.093	
B	7.798	9.093	
C	0.250	0.510	11
D	0.889	1.143	12
E	1.140	1.400	8
F	0.559	0.712	8
G	1.27 Typical		5, 9
H	1.630	2.540	

NOTES: See Page 11.

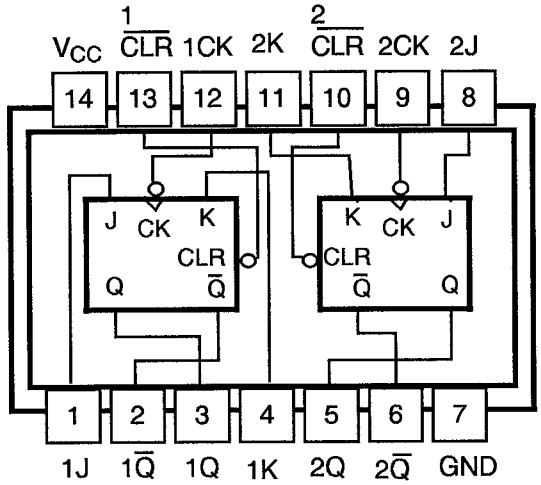
FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES TO FIGURES 2(a) to 2(d)

1. Index area; a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages, the index shall be as shown in Figure 2(d).
2. Dimension Q shall be measured at the point of exit of the lead from the body.
3. Dimension Q shall be measured from the seating plane to the base plane.
4. This dimension allows for off-centre lids, meniscus and glass overrun.
5. The true position pin or terminal spacing is 1.27mm between centrelines. Each pin centreline shall be located within ± 0.13mm of its true longitudinal position relative to Pins 1 and 14 .
6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ± 0.25mm of its true longitudinal position relative to Pins 1 and 14.
7. Applies to all four corners.
8. All leads or terminals.
9. 12 spaces for flat and dual-in-line packages.
   16 spaces for chip carrier packages.
10. Lead centre when α is 0°.
11. Index corner only - 2 dimensions.
12. 3 non-index corners - dimensions.

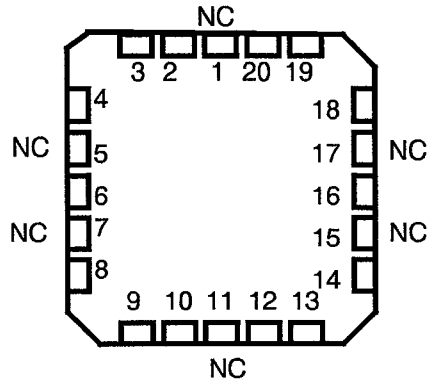
FIGURE 3 (a) - PIN ASSIGNMENT

DUAL-IN-LINE AND FLAT PACKAGE



(TOP VIEW)

CHIP CARRIER PACKAGE



(TOP VIEW)

FLAT PACKAGE AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

FLAT PACKAGE AND DUAL-IN-LINE PIN OUTS	1	2	3	4	5	6	7	8	9	10	11	12	13	14
CHIP CARRIER PIN OUTS	2	3	4	6	8	9	10	12	13	14	16	18	19	20

NOTES 1. All references throughout this specification relate to FLAT/DIL packages only.

FIGURE 3(b) - TRUTH TABLE

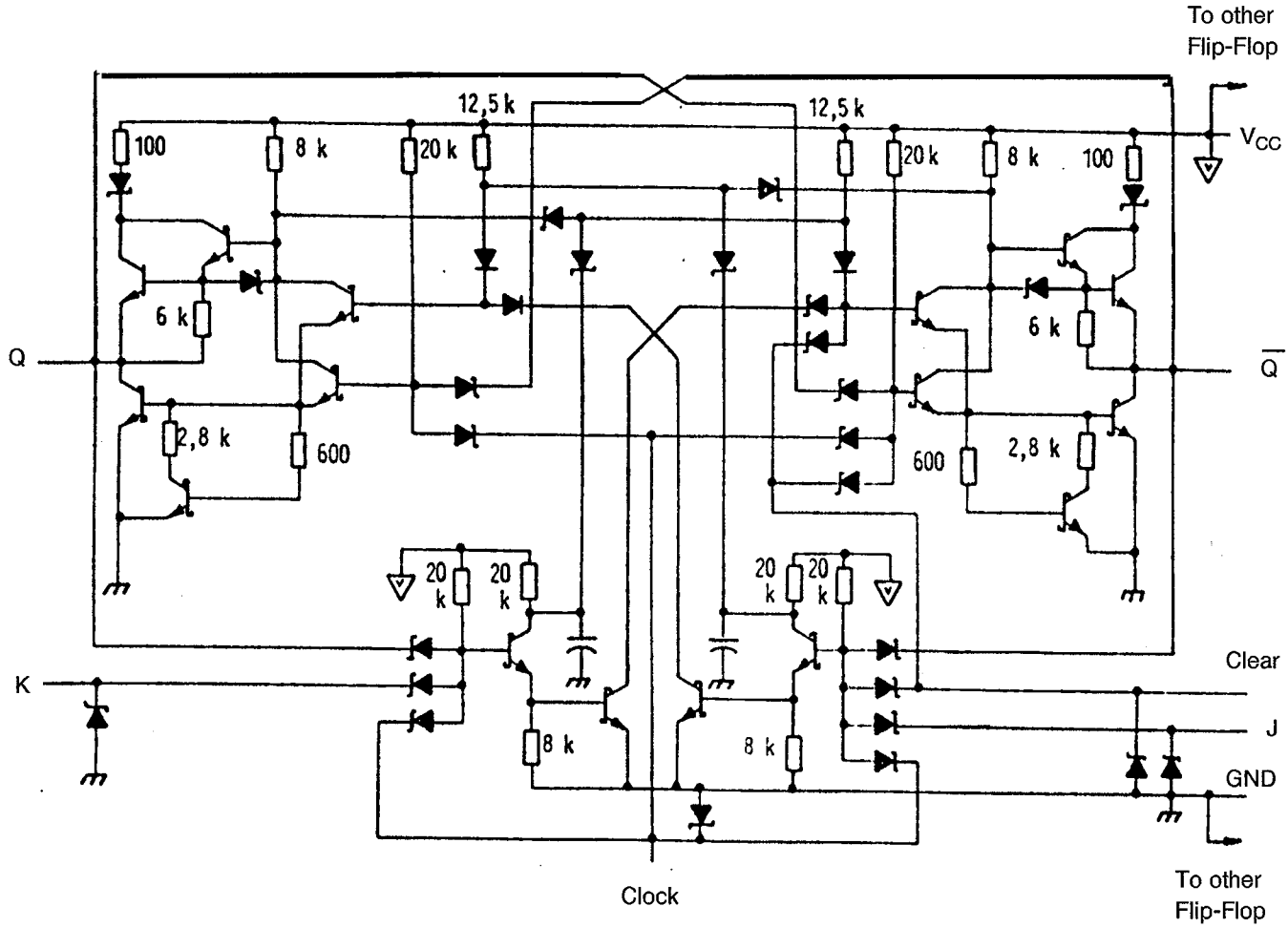
FUNCTION TABLE (each Flip-Flop)

INPUTS				OUTPUTS	
CLEAR	CLOCK	J	K	Q	$\overline{Q}$
L	X	X	X	L	H
H	↓	L	L	Q_0	$\overline{Q_0}$
H	↓	H	L	H	L
H	↓	L	H	L	H
H	↓	H	H	TOGGLE	
H	H	X	X	Q_0	$\overline{Q_0}$

NOTES

1. H = high level (steady state), L = low level (steady state), X = Irrelevant, Q_0 = level of Q before indicated steady state input conditions were established, ↓= transition from high to low level.

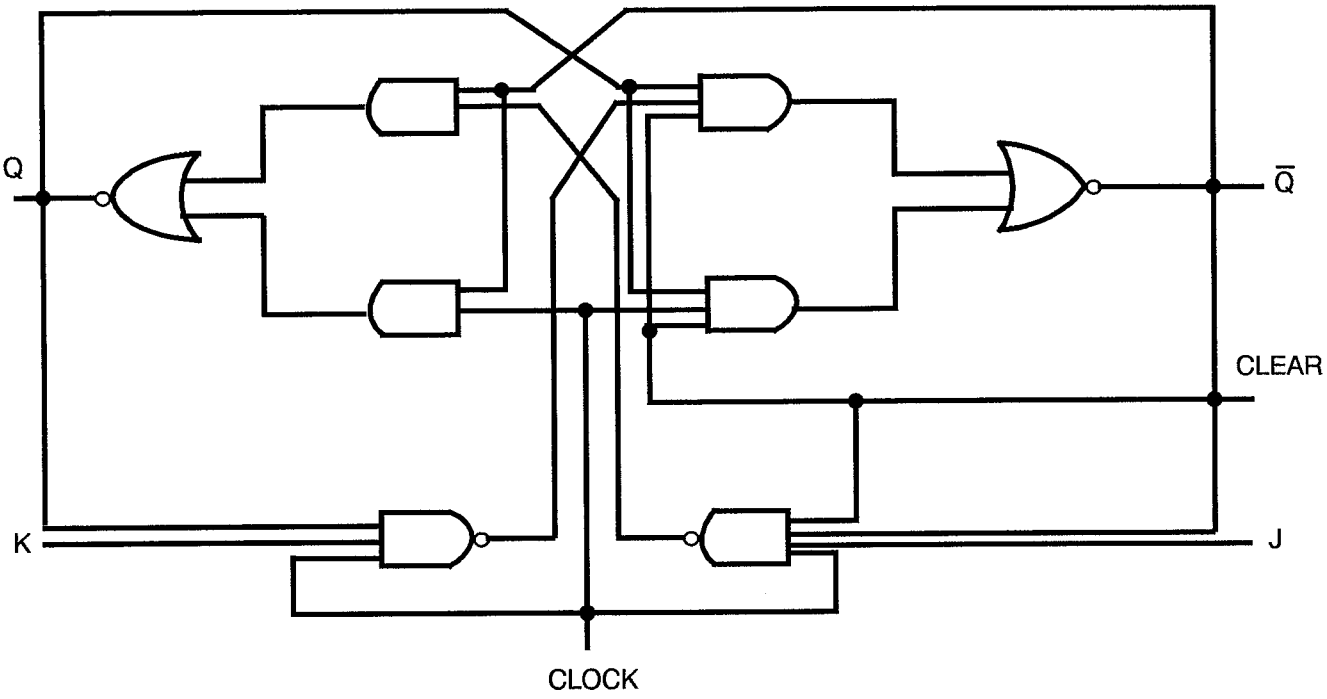
FIGURE 3(c) - CIRCUIT SCHEMATIC



NOTES

1. Resistor values are nominal.

FIGURE 3(d) - FUNCTIONAL DIAGRAM
(Each Flip-Flop)



2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

(a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.

(b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition the following abbreviations are used:

V_{IC} = Input Clamp Voltage

I_{CC} = Supply Current

V_{CC} = Supply Voltage

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Control

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

(a) Para. 7.1.1(a), High Temperature Reverse Bias test and subsequent electrical measurements related to this test shall be omitted.

(b) Para. 9.9.2, Electrical Measurements at High and Low Temperatures: Only a test result summary, based on go-no-go tests and presented in histogram form is required.

4.2.4 Deviations from Qualification Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.7 grammes for the flat package, 2.2 grammes for the dual-in-line package and 0.6 grammes for the chip carrier package.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

For dual-in-line packages, the lead material shall be either Type 'D' or Type 'G' with either Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

(a) Lead Identification.

(b) The SCC Component Number.

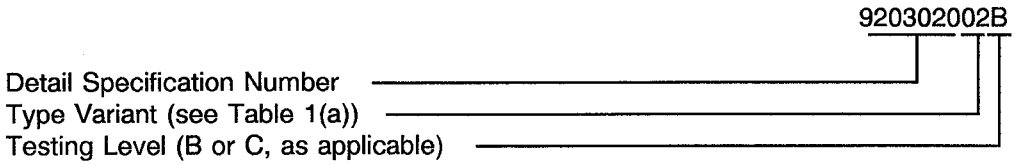
(c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(d).

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:-



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL CHARACTERISTICS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at T_{amb} = +22 ± 3 °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at T_{amb} = +125°C and -55°C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are as specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at T_{amb} = +22 ± 3 °C. The parameter drift values Δ applicable to the parameters scheduled shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuit for Power Burn-in

Circuits for use in performing the power burn-in test are shown in Figure 5 of this specification.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	Characteristics	Symbol	Test Method MIL-STD-883	Test Fig.	Test Conditions (Pins under Test)	Limits		Unit
						Min.	Max.	
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 5	Input Current High Level at J-K	I_{IH1}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 1-4-8-11)	-	20	µA
6 to 9	Input Current High Level at J-K (Max. Input Voltage)	I_{IH2}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 1-4-8-11)	-	100	µA
10 to 11	Input Current High Level at Clear	I_{IH3}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 10-13)	-	60	µA
12 to 13	Input Current High Level at Clear (Max. Input Voltage)	I_{IH4}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 10-13)	-	300	µA
14 to 15	Input Current High Level at Clock	I_{IH5}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 9-12)	-	80	µA
16 to 17	Input Current High Level at Clock (Max. Input Voltage)	I_{IH6}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 9-12)	-	400	µA
18 to 25	Input Clamp Voltage	V_{IC}	3008	4(b)	V_{CC} = 4.5V, I_{IN} = -18mA (Pins 1-4-8-9-10-11-12-13) Note 2	-	-1.5	V
26 to 29	Input Current Low Level at J-K	I_{IL1}	3009	4(c)	V_{CC} = 5.5V, V_{IN} = 0.4V (Pins 1-4-8-11)	-	-400	µA
30 to 33	Input Current Low Level at Clear and Clock	I_{IL2}	3009	4(c)	V_{CC} = 5.5V, V_{IN} = 0.4V (Pins 9-10-12-13)	-	-800	µA
34 to 37	Output Voltage Low Level	V_{OL}	3007	4(d)	V_{CC} = 4.5V, V_{IH} = 2.0V I_{OL} = 4mA, V_{IL} = 0.7V (Pins 2-3-5-6)	-	0.4	V

NOTES: See Page 20.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS (CONTINUED)

No.	Characteristics	Symbol	Test Method MIL-STD-883	Test Fig.	Test Conditions (Pins under Test)	Limits		Unit
						Min.	Max.	
38 to 41	Output Voltage High Level	V_{OH}	3006	4(e)	V_{CC} = 4.5V, V_{IH} = 2.0V V_{IL} = 0.7V, I_{OH} = -400µA (Pins 2-3-5-6)	2.5	-	V
42 to 45	Output Current Short Circuit	I_{OS}	3011	4(f)	V_{CC} = 5.5V (Pins 2-3-5-6) Note 3	-20	-100	mA
46 to 47	Supply Current	I_{CC}	3005	4(g)	V_{CC} = 5.5V. (Pin 14) Note 4	-	+6	mA

NOTES: See Page 20.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No.	Characteristics	Symbol	Test Method MIL-STD-883	Test Fig.	Test Conditions (Pins under Test) (Note 6)	Limits		Unit
						Min.	Max.	
48 to 55	Propagation Delay Low to High Level from Clear or Clock to Q or Q	t_{PLH}	3003	4(h)	V_{CC} = 5.0V R_L = 2kΩ C_L = 15pF (Pins 2-3-5-6)	-	20.0	ns
56 to 63	Propagation Delay High to Low Level from Clear or Clock to Q or Q	t_{PHL}				-	20.0	
64 to 67	Maximum Clock Frequency Note 5	f_{max}	-	4(h)	V_{CC} = 5.5V R_L = 2kΩ C_L = 15pF (Pins 2-3-5-6)	30	-	MHz

NOTES

1. Go-no-go test with V_{IL} = 0.3V; V_{IH} = 3.0V; trip point 1.5V.
2. All inputs and outputs not under test shall be open.
3. No more than one output should be shorted at a time, and only for 1 second maximum. I_{OS} measurement may be performed with V_{OUT} = 2.25V instead of 0V. In this case, the limits are divided by 2.
4. With all outputs open, ICC is measured with Q and $\overline{Q}$ outputs high in turn. At the time of measurement, the clock input is grounded.
5. This parameter shall be measured only when required by purchase order. In any case, the Manufacturer shall guarantee that the devices meet this requirement.
6. Propagation delay measurements shall be performed as a go-no-go test on a 100% basis. Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III burn-in test.

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, +125°C AND -55°C

No.	Characteristics	Symbol	Test Method MIL-STD-883	Test Fig.	Test Conditions (Pins under Test)	Limits		Unit
						Min.	Max.	
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 5	Input Current High Level at J-K	I_{IH1}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 1-4-8-11)	-	20	µA
6 to 9	Input Current High Level at J-K (Max. Input Voltage)	I_{IH2}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 1-4-8-11)	-	100	µA
10 to 11	Input Current High Level at Clear	I_{IH3}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 10-13)	-	60	µA
12 to 13	Input Current High Level at Clear (Max. Input Voltage)	I_{IH4}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 10-13)	-	300	µA
14 to 15	Input Current High Level at Clock	I_{IH5}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 2.7V (Pins 9-12)	-	80	µA
16 to 17	Input Current High Level at Clock (Max. Input Voltage)	I_{IH6}	3010	4(a)	V_{CC} = 5.5V, V_{IN} = 7.0V (Pins 9-12)	-	400	µA
18 to 25	Input Clamp Voltage	V_{IC}	3008	4(b)	V_{CC} = 4.5V, I_{IN} = -18mA (Pins 1-4-8-9-10-11-12-13) Note 2	-	-1.5	V
26 to 29	Input Current Low Level at J-K	I_{IL1}	3009	4(c)	V_{CC} = 5.5V, V_{IN} = 0.4V (Pins 1-4-8-11)	-	-400	µA
30 to 33	Input Current Low Level at Clear and Clock	I_{IL2}	3009	4(c)	V_{CC} = 5.5V, V_{IN} = 0.4V (Pins 9-10-12-13)	-	-800	µA
34 to 37	Output Voltage Low Level	V_{OL}	3007	4(d)	V_{CC} = 4.5V, V_{IH} = 2.0V I_{OL} = 4mA, V_{IL} = 0.6V (Pins 2-3-5-6)	-	0.4	V

NOTES: See Page 20.

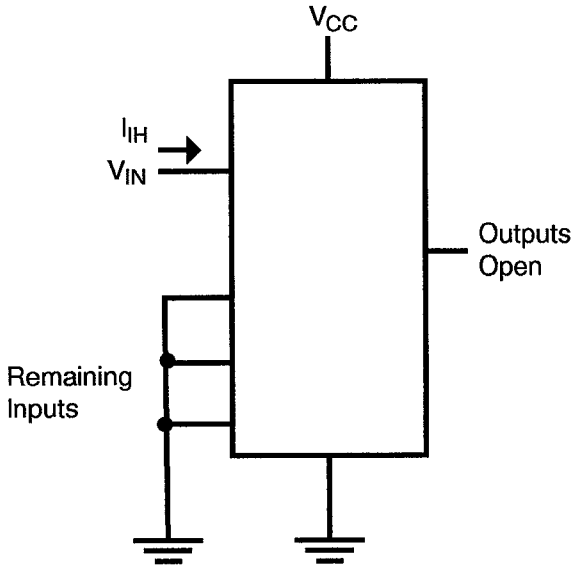
TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, +125°C AND -55°C (CONTINUED)

No.	Characteristics	Symbol	Test Method MIL-STD-883	Test Fig.	Test Conditions (Pins under Test)	Limits		Unit
						Min.	Max.	
38 to 41	Output Voltage High Level	V_{OH}	3006	4(e)	V_{CC} = 4.5V, V_{IH} = 2.0V V_{IL} = 0.6V, I_{OH} = -400µA (Pins 2-3-5-6)	2.5	-	V
42 to 45	Output Current Short Circuit	I_{OS}	3011	4(f)	V_{CC} = 5.5V (Pins 2-3-5-6) Note 3	-20	-100	mA
46 to 47	Supply Current	I_{CC}	3005	4(g)	V_{CC} = 5.5V. (Pin 14) Note 4	-	+6	mA

NOTES: See Page 20.

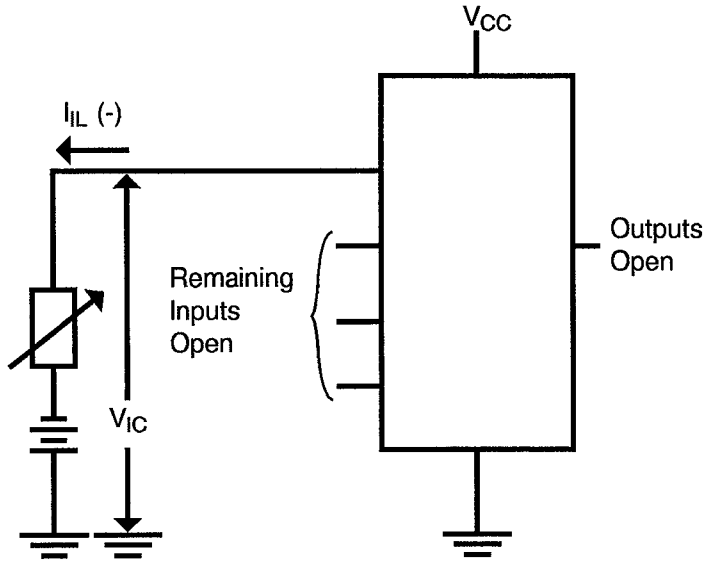
FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - HIGH LEVEL INPUT CURRENT



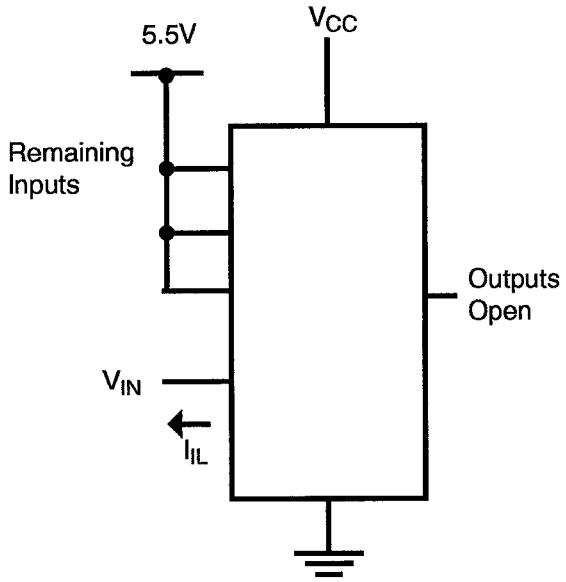
NOTES 1. Test each input separately.

FIGURE 4(b) - INPUT CLAMP VOLTAGE



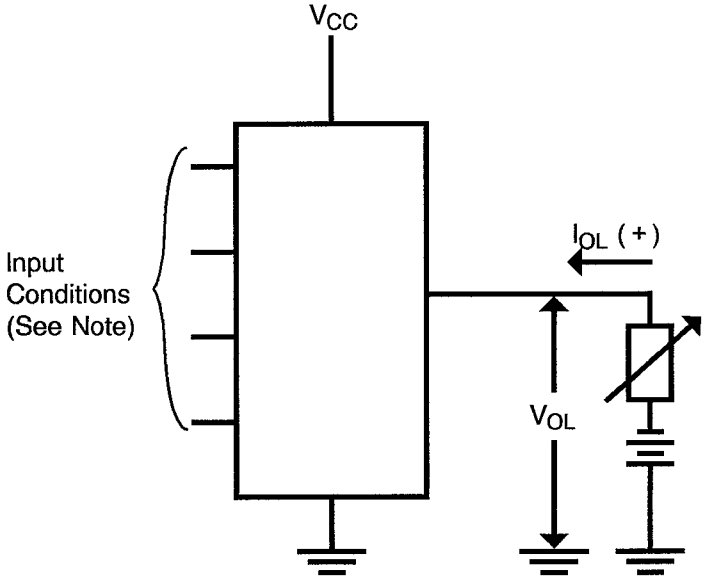
NOTES 1. Test each input separately.

FIGURE 4(c) - LOW LEVEL INPUT CURRENT



NOTES 1. Test each input separately.

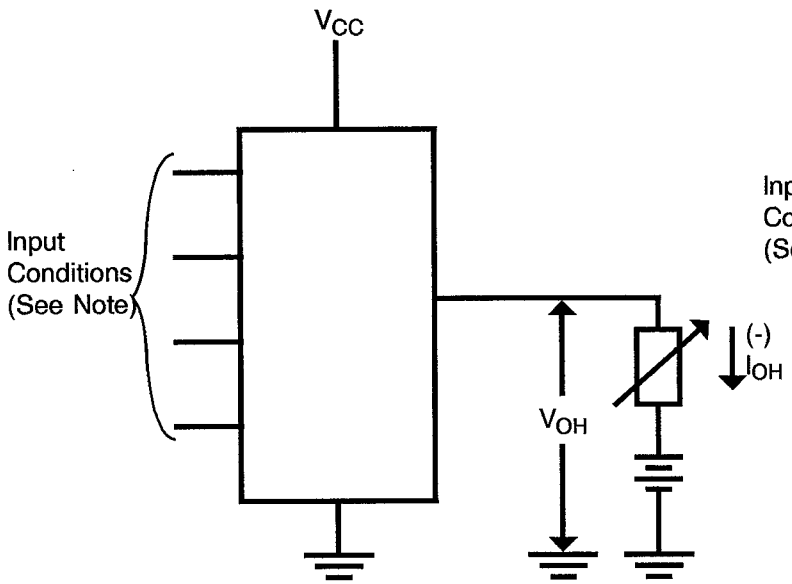
FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE



NOTES 1. Test per truth table.

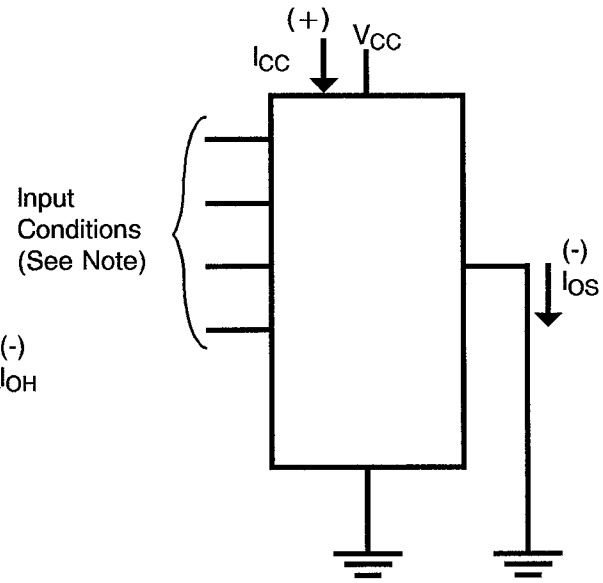
FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE



NOTES
1. Test per truth table.

FIGURE 4(f) - SHORT CIRCUIT OUTPUT CURRENT



NOTES
1. For $\overline{Q}$: CLK, CLR, J = 0; K = 4.5V
   For Q: K, $\overline{Q}$ = 0; J, CLR = 4.5V
   Apply pulse to CLK - amplitude 0 to 2.5V

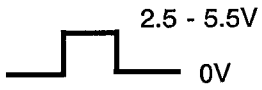
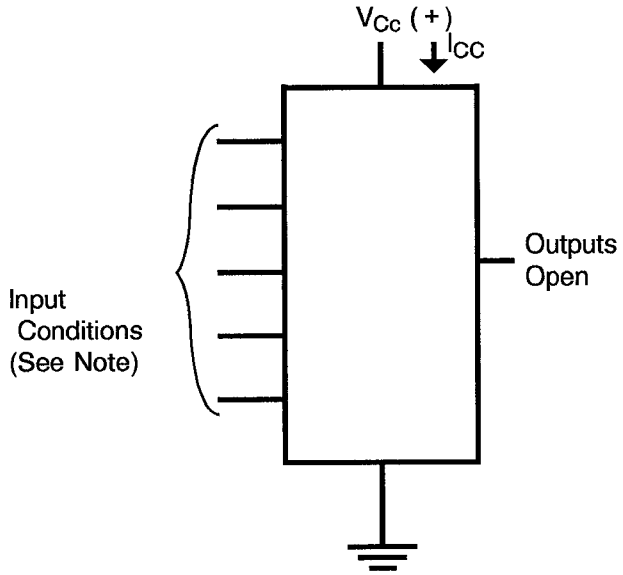


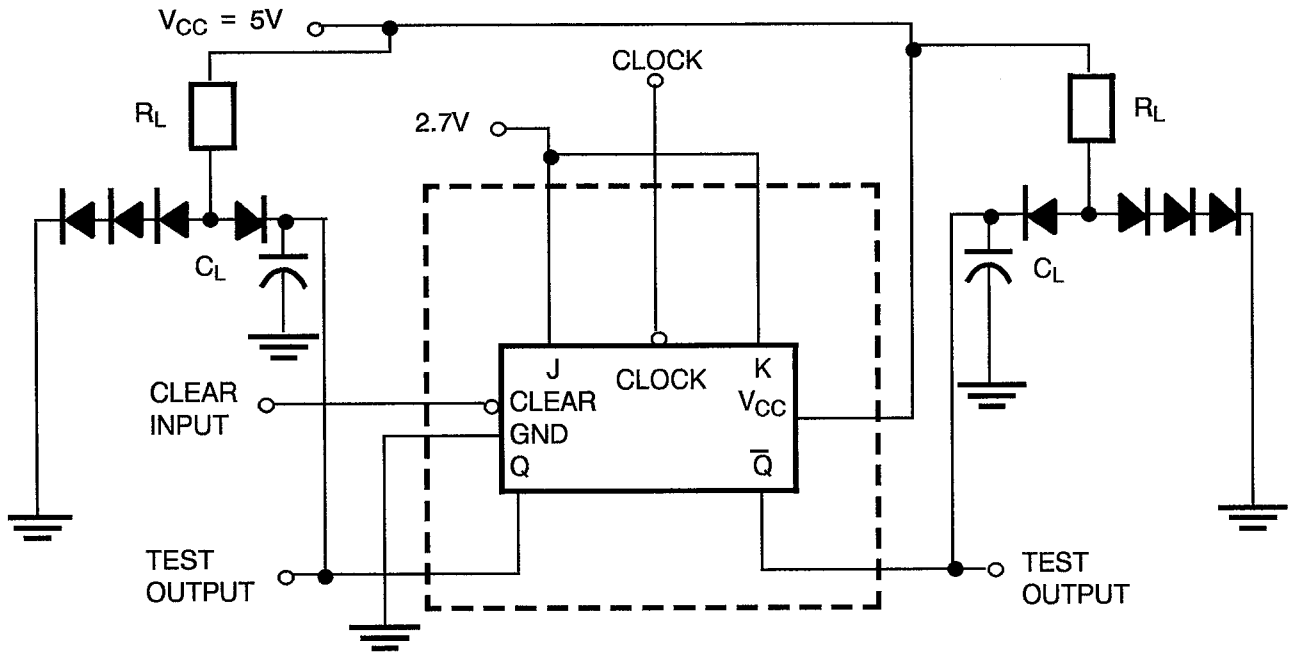
FIGURE 4(g) - SUPPLY CURRENT



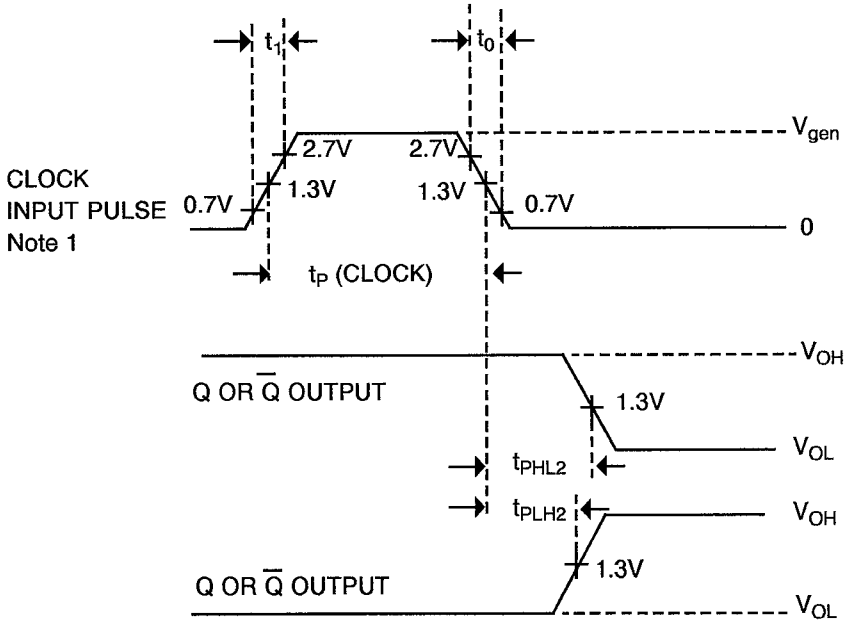
NOTES
1. See Note 4, Page 20.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(h) - DYNAMIC TEST AND SWITCHING WAVEFORMS



VOLTAGE WAVEFORMS



NOTES

1. Clock input characteristics for t_{PLH}, t_{PHL} (clock to output), V_{gen} = 3V, t_1 < 15ns, t_0 < 6ns, t_P (clock) = 25ns and PRR < 1MHz. All J and K inputs are at 2.5V. When testing f_{MAX} the clock input characteristics are V_{gen} = 3V, t_1 = t_0 < 10ns, t_P (clock) = 20ns and PRR < 1MHz.
2. All diodes are 1N916 or 1N3064.
3. C_L = 15pF minimum, including scope probe, wiring and stray capacitance without package in test fixture.
4. R_L = 2kΩ ±5%.

TABLE 4 - PARAMETER DRIFT VALUES

No.	Characteristics	Symbol	Spec. and/or Test Method	Test Conditions	Change Limits (Δ)	Unit
2 to 5	Input Current High Level	I_{IH}	As per Table 2	As per Table 2	±0.5 or ± 20 (1)	µA %
26 to 29	Input Current Low Level	I_{IL}	As per Table 2	As per Table 2	±18	µA
34 to 37	Output Voltage Low Level	V_{OL}	As per Table 2	As per Table 2	± 60	mV
38 to 41	Output Voltage High Level	V_{OH}	As per Table 2	As per Table 2	±240	mV

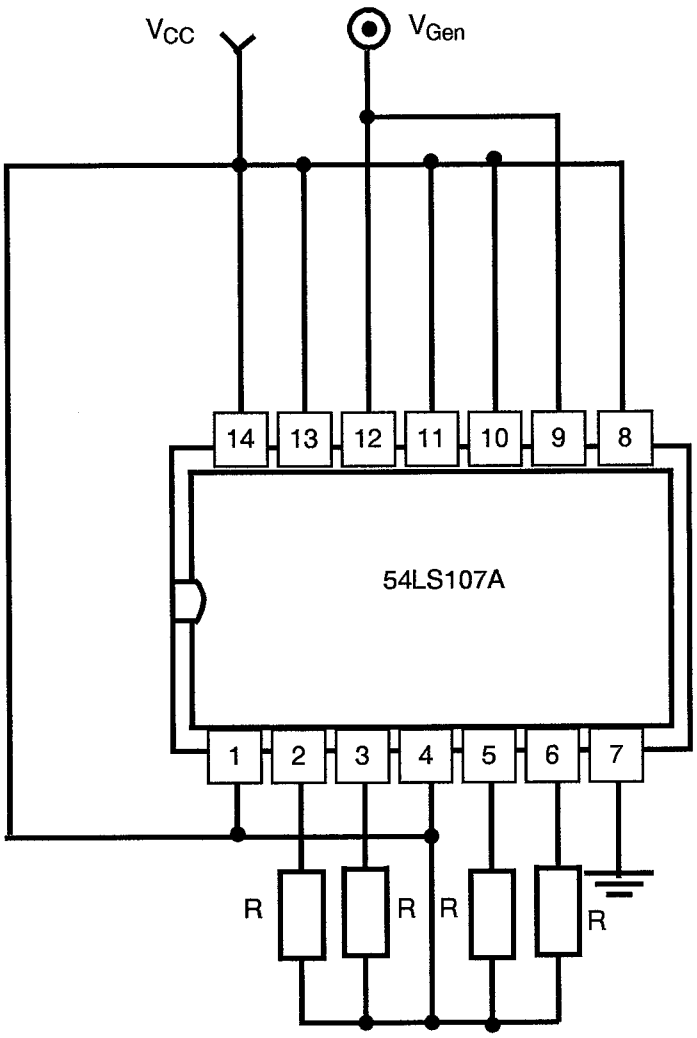
NOTES 1. Whichever is greater, referred to the initial value.

TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

No.	Characteristics	Symbol	Condition	Unit
1	Ambient Temperature	T_{amb}	+125(+0-5)	°C
2	Power Supply Voltage	V_{CC}	+5(+0.5-0)	V
3	Pulse Voltage	V_{GEN}	0.5 max to 3.0 min	V
4	Frequency	f	100 (Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	t_r	50 max.	µs
7	Fall Time	t_f	50 max.	µs
8	Duty Cycle	-	20 min.	%

NOTES 1. Tolerance ±10%.

FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST



NOTES
1. R = 1.2KΩ.

4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION No. 9000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22 ±3 °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22 ±3 °C.

4.8.4 Conditions for Operating Life Test

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 Electrical Circuits for Operating Life Tests

Circuits for use in performing the operating life test are shown in Figure 5 of this specification.

4.8.6 Conditions for High Temperature Storage Test

The requirements for high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be T_{amb} = +150(+0-5) °C.

TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINT AND ON COMPLETION OF ENDURANCE TESTS

No.	Characteristics	Symbol	Spec. and/or Test Method	Test Conditions	Change Limits		Unit
					(Δ)	Absolute	
2 to 5	Input Current High Level 1	I_{IH1}	As per Table 2	As per Table 2	±1.0	-	µA
6 to 9	Input Current High Level 2	I_{IH2}	As per Table 2	As per Table 2	-	100	µA
26 to 29	Input Current Low Level	I_{IL}	As per Table 2	As per Table 2	±12	-	µA
34 to 37	Output Voltage Low Level	V_{OL}	As per Table 2	As per Table 2	± 60	-	mV
38 to 41	Output Voltage High Level	V_{OH}	As per Table 2	As per Table 2	±240	-	mV
46 to 47	Supply Current	I_{CC}	As per Table 2	As per Table 2	± 20	-	%

APPENDIX 'A'

AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (FRANCE)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 4.2.1	Scanning Electron Microscope (S.E.M.) Inspection may be performed using TIF document TIF 3.61.610.001.
Para. 4.2.2	Prior to Die Shear Test TIF may perform a Radiographic Inspection on the randomly chosen samples to be subjected to this test, using TIF document TIF 50.42-3002.
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TIF 50.42-3002.